

Please amend the present application as follows:

Specification

The following is a marked-up version of the specification with the language that is underlined (“___”) being added and the language that contains strikethrough (“—”) being deleted:

Please amend paragraph [0002] as follows:

This application is related to copending U.S. Utility patent application ~~entitled~~
~~“Piezoelectric On Semiconductor On Insulator Microelectromechanical Resonators and~~
~~Methods of Fabrication,”~~ docket No. ~~62020-1430~~ having Serial No. 10/631,948, filed on the
same date.

Please amend paragraph [0005] as follows:

Micro-electro-mechanical (MEMS) resonators are a potential candidate to replace
current off-chip frequency selective mechanical components such as crystal, ceramic and
SAW (Surface Acoustic Wave) devices in wireless communication systems. High quality
factors, small size and compatibility with integrated circuit (IC) integration are some of the
advantages silicon MEMS capacitive resonators provide over their bulk-component
counterparts. Extension of the frequency range of capacitive MEMS resonators into the giga-
Hertz (GHz) range requires process technologies that can yield 10-100 nanometer capacitive
gap spacings disposed between a high quality factor (Q) resonating structure and ~~[[a]]~~
corresponding drive and sense electrodes. Quality factor can generally be described as a
measure of energy stored in a system divided by the energy dissipated in the system. Quality
factor can be characterized in terms of frequency response of a resonator, such as the ratio of
the center frequency (f₀) to the 3-dB (decibel) bandwidth of the resonator device.

Please amend paragraph [0009] as follows:

~~Briefly described, one embodiment of the MEMS capacitive resonator, among others, comprises a semiconductor resonating member and a polysilicon electrode capacitively coupled to the semiconductor resonating member.~~

Please amend paragraph [0010] as follows:

The present invention can also be viewed as providing methods for fabricating the a MEMS capacitive resonator. In this regard, one embodiment of such a method, among others, can be broadly summarized by the following steps: forming trenches in a substrate; conformally coating the substrate with an oxide; filling the coated trenches with polysilicon; patterning the polysilicon; releasing a resonator resonating structure derived from the substrate; and removing the conformally coated oxide.